

MOSFETs Silicon P-Channel MOS (U-MOSVI)

TPCP8105

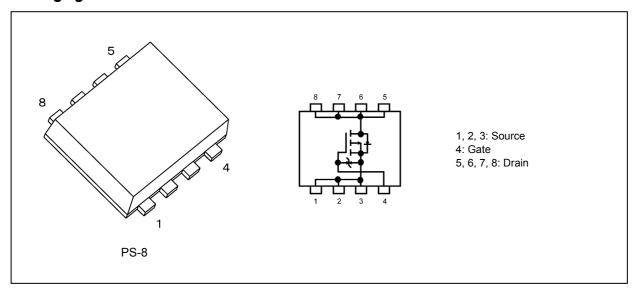
1. Applications

- · Lithium-Ion Secondary Batteries
- · Power Management Switches
- · Notebook PCs

2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 13.8 \text{ m}\Omega$ (typ.) ($V_{GS} = -4.5 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \mu A \text{ (max) (V}_{DS} = -20 \text{ V)}$
- (4) Enhancement mode: V_{th} = -0.5 to -1.2 V (V_{DS} = -10 V, I_{D} = -1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	-20	V
Gate-source voltage			V _{GSS}	±12	
Drain current (DC)		(Note 1)	I _D	-7.2	Α
Drain current (pulsed)		(Note 1)	I _{DP}	-28.8	
Power dissipation	(t = 5 s)	(Note 2)	P_{D}	1.68	W
Power dissipation	(t = 5 s)	(Note 3)	P_{D}	0.84	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	33.0	mJ
Avalanche current			I _{AR}	-7.2	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R _{th(ch-a)}	74.4	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R _{th(ch-a)}	148.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = -16 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_{G} = 25 Ω , I_{AR} = -7.2 A

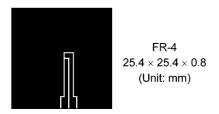


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

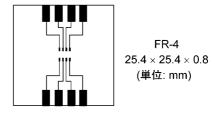


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	_	-	-10	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-20			V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 8 \text{ V}$	-12			
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-0.5		-1.2	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = -1.8 \text{ V}, I_D = -1.8 \text{ A}$	_	28	60	mΩ
		V_{GS} = -2.0 V, I_D = -1.8 A	_	25	45	
		$V_{GS} = -2.5 \text{ V}, I_D = -3.6 \text{ A}$	_	17.9	23	
		V_{GS} = -4.5 V, I_D = -3.6 A	_	13.8	17	

Note 5: If a forward bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	2280	_	pF
Reverse transfer capacitance	C _{rss}		_	296	_	
Output capacitance	C _{oss}		_	340	_	
Switching time (rise time)	t _r	See Figure 6.2.1.	_	7.2	_	ns
Switching time (turn-on time)	t _{on}		_	15	_	
Switching time (fall time)	t _f		_	71	_	
Switching time (turn-off time)	t _{off}		_	241	_	

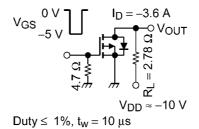


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}$ C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx -16 \text{ V}, V_{GS} = -5 \text{ V}, I_D = -7.2 \text{A}$	_	28		nC
Gate-source charge 1	Q _{gs1}		_	5		
Gate-drain charge	Q _{gd}		_	7	_	

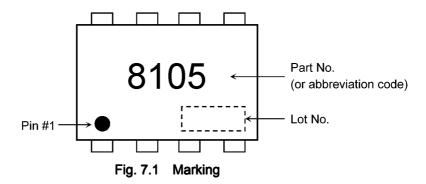
6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	_	_	_	-28.8	Α
Diode forward voltage		V_{DSF}	$I_{DR} = -7.2 \text{ A}, V_{GS} = 0 \text{ V}$	-		1.2	V

Note 6: Ensure that the channel temperature does not exceed 150°C.



7. Marking



Rev.2.0

8. Characteristics Curves (Note)

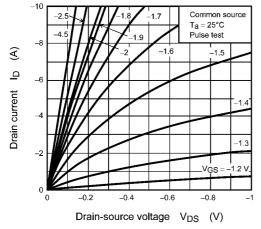
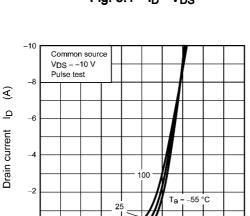


Fig. 8.1 I_D - V_{DS}



 $\label{eq:Gate-source} \begin{array}{ccc} \text{Gate-source voltage} & \text{V}_{GS} & \text{(V)} \\ & & \textbf{Fig. 8.3} & \textbf{I}_{\textbf{D}} \textbf{-} \textbf{V}_{\textbf{GS}} \end{array}$

0

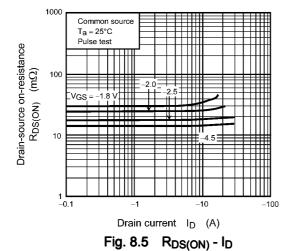


Fig. 8.2 I_D - V_{DS}

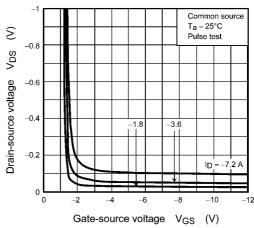


Fig. 8.4 V_{DS} - V_{GS}

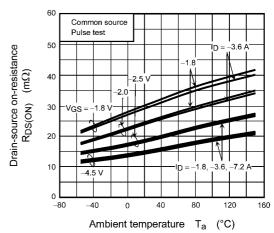


Fig. 8.6 R_{DS(ON)} - T_a

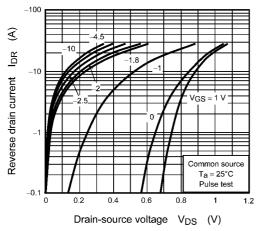


Fig. 8.7 IDR - VDS

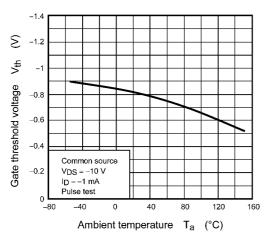


Fig. 8.9 V_{th} - T_a

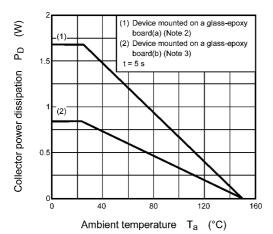


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

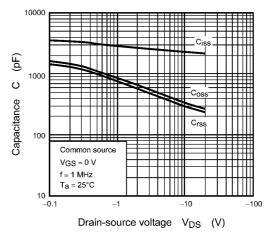


Fig. 8.8 Capacitance - V_{DS}

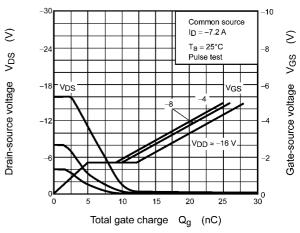


Fig. 8.10 Dynamic Input/Output Characteristics

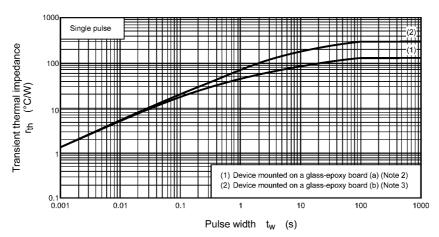


Fig. 8.12 r_{th} - t_w (Guaranteed Maximum)

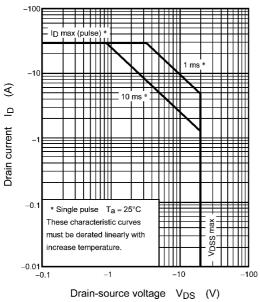


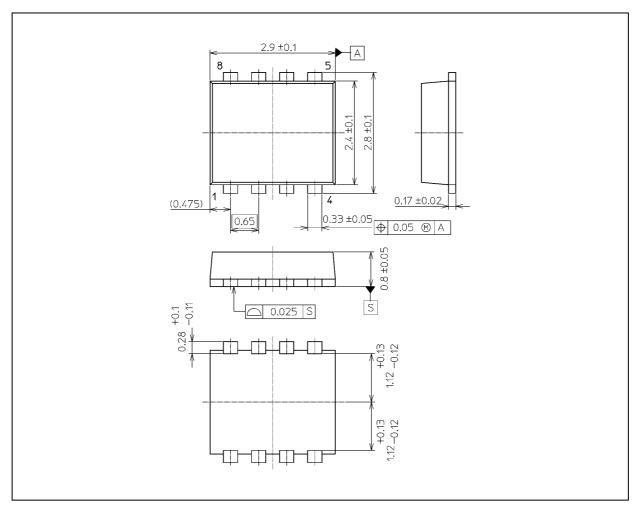
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.017 g (typ.)

	Package Name(s)
TOSHIBA: 2-3V1S	
Nickname: PS-8	

Rev.2.0



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